

# RB521S-30-HAF

## Silicon Epitaxial Planar Schottky Barrier Diode

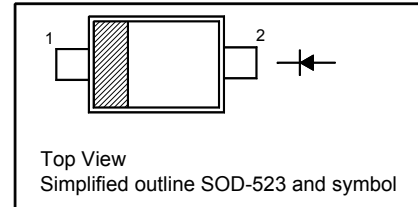
for low current rectification and high speed switching applications

### Features

- Extremely small surface mounting type
- Halogen and Antimony Free(HAF), RoHS compliant

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

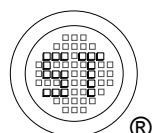


### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	30	V
Average Forward Current	$I_{F(AV)}$	200	mA
Peak Forward Surge Current (60 Hz for Cyc.)	$I_{FSM}$	1	A
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 40 to + 125	$^\circ\text{C}$

### Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 150 \mu\text{A}$	$V_{(BR)R}$	30	-	V
Forward Voltage at $I_F = 200 \text{ mA}$	$V_F$	-	0.5	V
Reverse Current at $V_R = 10 \text{ V}$	$I_R$	-	30	$\mu\text{A}$



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## Electrical Characteristics Curves

Fig 1. Reverse Characteristic Curve

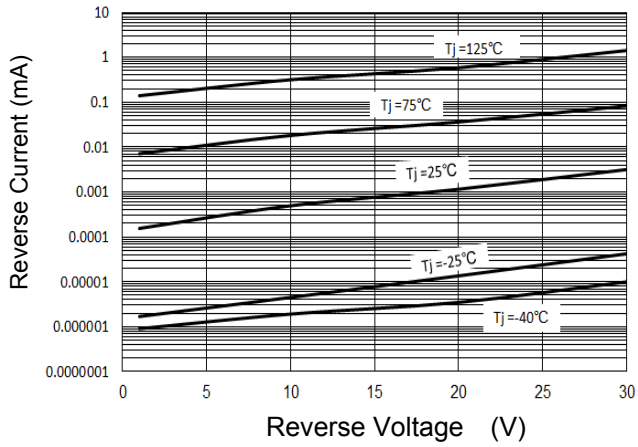


Fig 2. Forward Characteristic Curve

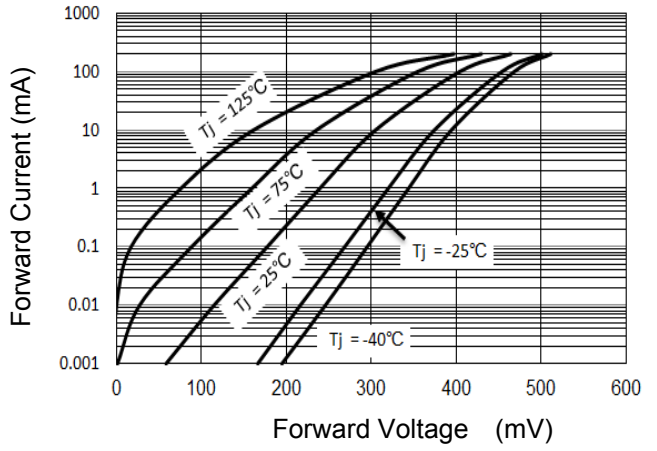


Fig 3. Junction Capacitance

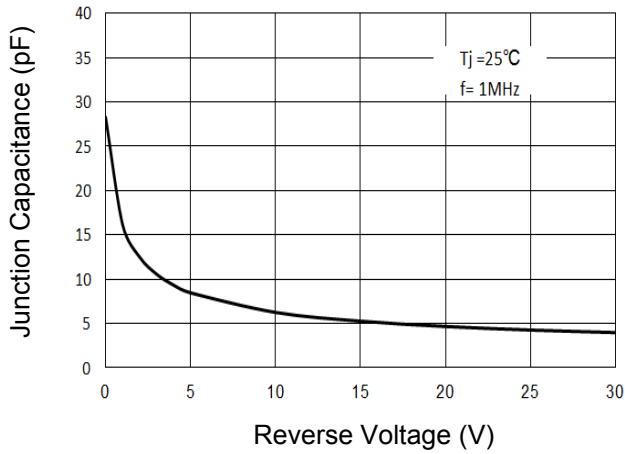
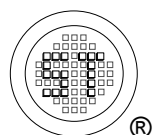
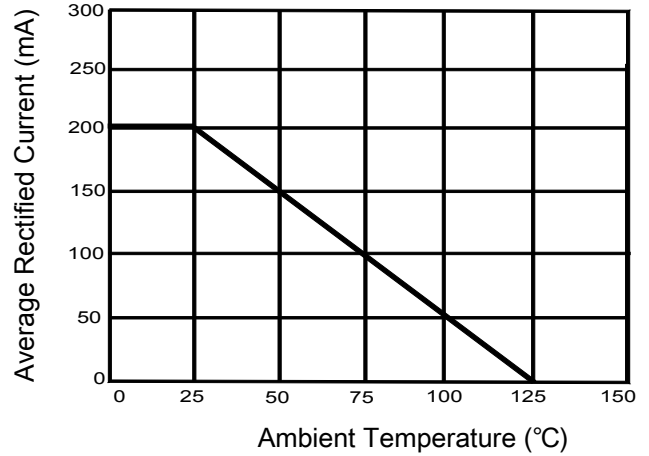


Fig 4. Average Rectified Current Derating Curve

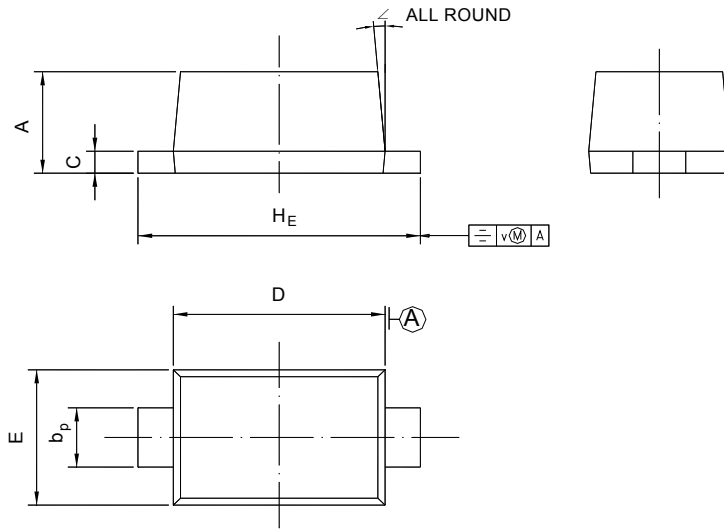


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## PACKAGE OUTLINE

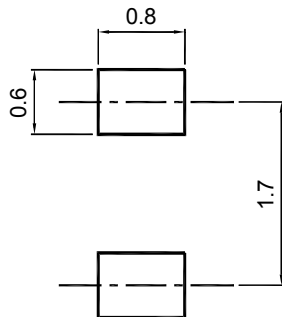
Plastic surface mounted package; 2 leads

SOD-523



UNIT	A	b <sub>p</sub>	C	D	E	H <sub>E</sub>	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°

### Recommended Soldering Footprint



### Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOD-523	8	4 ± 0.1	0.157 ± 0.004	178	7	4,000

### Marking information

- " C " = Part No.
  - " III " = Cathode line
  - " • " = HAF (Halogen and Antimony Free)
- Font type: Arial

